

Année	Auteurs	Titre	Revue	Référence
2008	F. Balestra (invited paper)	New Semiconductor Devices	Acta Physica Polonica A	Vol. 114, no.5, pp. 945-974, 2008
2008	K. Bennamane, M. DeMichielis, G. Ghibaudo, D. Esseni	Extraction of eta parameter characterising $\mu(\text{eff})$ against E-eff curves in strained Si nMOS devices	Electronics Letters	Vol 44, 1219-1220 (2008)
2008	L. Zafari, J.Jomaah, G. Ghibaudo	Modeling and simulation of coupling effect on low frequency noise in advanced SOI MOSFETS	Fluctuations and Noise Lett.	Vol. 8, no.1, pp. L87-L94 (Mar. 2008)
2008	L. Zafari, J. Jomaah, G. Ghibaudo, O. Faynot	Analysis of spatial and energy slow trap profile in HfO ₂ /SiO ₂ metal-oxide-silicon devices by low frequency noise measurements	Fluctuations and Noise Lett.	Vol. 8, no.2, pp. L99-L105 (June 2008)
2008	N. Rodriguez, F. Gamiz, R. Clerc, G. Ghibaudo, S. Cristoloveanu	The Quantization Impact of Accumulated Carriers in Silicide-Gated MOSFETs	IEEE Electron Device Letters	Vol. 29, no. 6, pp. 628-631 (June 2008)
2008	A.Cathignol, B. Cheng, D. Chanemougame, A. R. Brown, K. Rochereau, G. Ghibaudo, A. Asenov,	Quantitative Evaluation of Statistical Variability Sources in a 45nm Technological Node LP N-MOSFET	IEEE Electron Device Letters	Vol. 29, no.6, pp. 609-611 (June 2008)
2008	C. Le Royer, B. Vincent, L. Clavelier, J-F. Damlencourt, C. Tabone, P. Batude, D. Blachier, R. Truche, Y. Campidelli, Q.T. Nguyen, S. Cristoloveanu, S. Soliveres, G. Le Carval, F. Boulanger, T. Billon, D. Bensahel, S. Deleonibus	High-K and metal-gate pMOSFETs on GeOI obtained by Ge enrichment: analysis of ON and OFF performances	IEEE Electron Device Letters	Vol. 29, no.6, pp. 635-637 (June 2008)
2008	M. Bawedin, S. Cristoloveanu, D. Flandre	A capacitor-less 1T-DRAM on SOI based on double gate operation	IEEE Electron Device Letters	Vol. 29, no.7, pp. 795-798 (July 2008)
2008	A. Asenov, A. Cathignol, B. Cheng, K. P. McKenna, A. R. Brown, A. L. Shluger, G. Ghibaudo	Origin of the Asymmetry in the Statistical Variability of n- and p-channel Poly Si Gate Bulk MOSFETs.	IEEE Electron Device Letters	Vol. 29, no.8, pp. 913-915 (Aug. 2008)
2008	A. Tsormpatzoglou, C. A. Dimitriadis, R. Clerc, G. Pananakakis, and G. Ghibaudo	Threshold Voltage Model for Short-Channel Undoped symmetrical Double-Gate MOSFETs	IEEE Trans. Electron Devices	Vol. 55, 2512 (2008).
2008	A. Tsormpatzoglou, C. A. Dimitriadis, R. Clerc, G. Pananakakis, and G. Ghibaudo	Semi-analytical modelling of short channel effects in lightly doped silicon tri-gate MOSFETs	IEEE Trans. Electron Devices	Vol. 55, no.10, pp. 2623-2631 (Oct. 2008)

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2008	S. Poli, M.G. Pala, T. Poiroux, S. Deleonibus, and G. Bacarani	Size Dependence of Surface-Roughness-Limited Mobility in Silicon-Nanowire FETs	IEEE Trans. Electron Devices	Vol. 55, no.11, pp. 2968-2976 (2008)
2008	K. Rogdakis, S.-Y. Lee, M. Bescond, S.-K. Lee, E. Bano and K. Zekentes	3C-Silicon Carbide nanowire FET: An experimental and theoretical Approach	IEEE Trans. Electron Devices	Vol. 55, no.8, pp.1970-1976 (Aug. 2008)
2008	K. Zekentes, N. Camara, V.V. Basanets, M.S. Boltovets, V.A. Kryvutsa, V.O. Orechovskij, V.I. Simonchuk, A.V. Zorenko and E. Bano	Microwave Modulators based on 4H-SiC p-i-n Diodes	IEEE Trans. Microwave Theory and Techniques	Vol. 56, no.4, pp. 803-808 (April 2008)
2008	F.E. Mamouni, S.K. Dixit, R.D. Scrimpf, P.C. Adell, IS Esqueda, M.L. McLain, H.J. Barnaby, S. Cristoloveanu, W.Z. Xiong	Gate-Length and Drain-Bias Dependence of Band-to-Band Tunneling-Induced Drain Leakage in Irradiated Fully Depleted SOI Devices	IEEE Trans. Nuclear Science	Vol. 55, no.6, pp. 3259-3264 (June 2008)
2008	D. Fleury, A. Cros, K. Romanjek, D. Roy, F. Perrier, B. Dumont, H. Brut and G. Ghibaudo	Automatic Extraction Methodology for Accurate Measurements of Effective Channel Length on 65nm MOSFET Technology and Below	IEEE Trans. Semiconductor Manufacturing	Vol. 21, no.4, pp. 504-512 (Nov. 2008)
2008	Bjoern Ebert, Torsten Reich, Thomas Ortlepp, Pascal Febvre and F. H. Uhlmann	Influence of trapped flux on critical currents of Josephson junctions	IEICE Electron. Express	Vol. 5, n° 11, pp.431-436 (2008)
2008	David Bouis and Pascal Febvre	Antennas for Short Distance Communications in Cryogenic Environment	Int. J. Infrared Millimeter Waves	Vol. 29, n°12, pp. 1156-1162 (Dec. 2008)
2008	C. Buran, M. G. Pala, M. Bescond and M. Mouis	Full-three dimensional quantum approach to evaluate the surface-roughness-limited magnetoresistance mobility in SNWT	J. Computational Electronics	Vol. 7, no.3, 1569-1572 (2008)
2008	E. Rauwel, M.-G. Willinger, F. Ducroquet, P. Rauwel, I. Matko, D. Kiselev, I.K. Bdikin, N. Pinna	Carboxylic acids as oxygen sources for the atomic layer deposition of high-k metal oxides	J. Phys. Chem. C	Vol. 112, no.33,12754-12759 (2008)
2008	Seung-Yong Lee, Chan-Oh Jang, Dong-Joo Kim, Jung-Hwan Hyung, Konstantinos Rogdakis, Edwige Bano, Konstantinos Zekentes, and Sang-Kwon Lee	Fabrication of Ion-implanted Si Nanowire p-FETs	J. Phys. Chem. C	Vol. 112, p.13287-13291 (2008)

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2008	A. Ohata, C. Gallon, C. Fenouillet-Beranger, S. Cristoloveanu	Investigation of mobility enhancement effect in process-induced strained ultrathin silicon-on-insulator metal-oxide-semiconductor field-effect transistors	Japanese Journal of Applied Physics	Vol. 47, no.4, pp. 2124-2126 (Apr. 2008)
2008	N. Archontas, N. Georgoulas, C.A. Dimitriadis, F. Templier, M. Oudwan, G. Kamarinos	Two-dimensional simulation and modeling of the electrical behavior in nanocrystalline silicon thin film transistors	Journ. Appl. Phys.	Vol. 103, no.10, 104507:1-7 (May 2008)
2008	A.T. Hatzopoulos, D.H. Tassis, N. Arpatzani, C.A. Dimitriadis, F. Templier, M. Oudwan, G. Kamarinos	Stability of n-channel a-Si:H/nc-Si:H bilayer thin film transistors under dynamic stress	Journ. Appl. Phys.	Vol. 103, no.8, pp.084514:1-5 (Apr. 2008)
2008	T. Reich, P. Febvre, Th. Ortlepp, F.H. Uhlmann, J. Kunert, R. Stolz and H.G. Meyer	Experimental study of a hybrid SFQ digital SQUID magnetometer	Journ. Appl. Phys.	Vol. 104, no.2, pp. 024509:1-9 (July 2008)
2008	K. Huet, D. Querlioz, W. Chaisantikulwat, J. Saint-Martin, A. Bournel, M. Mouis, P. Dollfus	Monte Carlo study of apparent magnetoresistance mobility in nanometer scale metal oxide semiconductor field effect transistors	Journ. Appl. Phys.	Vol. 104, no.4, pp. 044504:1-7. Publisher: AIP, USA (15 Aug. 2008)
2008	T.V. Chandrasekhar Rao, J. Antoszewski, L. Faraone, S. Cristoloveanu, T. Nguyen, P. Gentil, N. Bresson, F. Allibert	Transport measurements in silicon-on-insulator films: Comparison of Hall effect, mobility spectrum, and pseudo-metal-oxide-semiconductor-field-effect-transistor techniques	Journ. Appl. Phys.	Vol.103, no.3, pp. 034503:1-5 (Fev. 2008)
2008	G. Beylier, S. Bruyère, P. Mora, and G. Ghibaudo	New Characterization Methodology of Borderless Silicon Nitride Charge Kinetics Using C-V Hysteresis Loops	Journal of The Electrochemical Society	Vol. 155, H273-H279 (2008).
2008	J. Lee, I. Han, B.Y. Yu, G.C. Yi, G. Ghibaudo	Physical Understanding of the Hooge Parameter in ZnO Nanowire Devices	Journal of the Korean Physical Society	Vol. 53, pp. 339-342 (2008)
2008	F. Balestra, E. Parker, D. Leadley, S. Mantl, E. Dubois, O. Engstrom, R. Clerc, S. Cristoloveanu, H. Kurz, J.P. Raskin, M. Lemme, A. Ionescu, K.E. Moselund, K. Boucart, E. Kasper, A. Karmous, M. Baus, B. Spangenberg, M. Ostling, E. Sangiorgi, G. Ghibaudo and D. Flandre (Invited paper)	Silicon-based nanostructures and nanodevices for long-term nanoelectronics applications	Material Science in Semiconductor Processing	Vol. 11, pp. 148-159 (2008)

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2008	G. Molas, M. Bocquet, J. Buckley, H. Grampeix, M. Gély, J.P. Colonna, F. Martin, P. Brianceau, V. Vidal, C. Bongiorno, S. Lombardo, G. Pananakakis, G. Ghibaudo, B. De Salvo, S. Deleonibus	Evaluation of HfAlO high-k materials for control dielectric applications in non-volatile memories	Microelectronic Engineering	Vol. 85, no. 12, pp. 2393-2399 (Dec. 2008)
2008	G. Beylier, S. Bruyère, D. Benoit, G. Ghibaudo	Impact of Silicon nitride CESL on NLDEMOS transistor reliability	Microelectronics Reliability	Vol. 48, no. 8-9, pp. 1539-1543 (Aug.-Sept. 2008)
2008	N. Arpatzianis, A. T. Hatzopoulos, D.H. Tassis, C.A. Dimitriadis, F. Templier, M. Oudwan, G. Kamarinos	Degradation of n-channel a-Si:H/nc-Si:H bilayer thin film transistors under DC electrical stress	Microelectronics Reliability	Vol. 48, no.4, p. 531-536 (Apr. 2008)
2008	M. Diop, N. Revil, M. Marin, F. Monsieur, P. Chevalier, G. Ghibaudo	Impact of inside spacer process on fully self-aligned 250 GHz SiGe:C HBTs reliability performances: a-Si vs. Nitride	Microelectronics Reliability	Vol. 48, no.8-9, pp.1198-1201 (Sept.-Aug. 2008)
2008	Jungil Lee, Byung-Yong Yu, Chul Ho Lee, Gyu-Chul Yi, Seung Hun Son, Gyu-Tae Kim, G. Ghibaudo	Low-frequency noise characterization of ZnO nanorod back-gate field-effect transistor structure	Physica E	Vol. 40, 2147-2149 (2008)
2008	A. Tsormpatzoglou, C.A. Dimitriadis, R. Clerc, G. Pananakakis, G. Ghibaudo	Semi-analytical modelling of short channel effects in Si Double-Gate, Tri-Gate and Gate-All-Around MOSFETs	Physica Stat. Sol. (c)	Vol. 5, no.12, p. 3605-3608 (2008)
2008	M. G. Pala, B. Hackens, F. Martins, H. Sellier, V. Bayot, S. Huant, T. Ouisse	Local density of states in mesoscopic samples from scanning gate microscopy	Physical Review B	Vol. 77, no.12, 125310 (2008)
2008	M. Governale, M.G. Pala and J. König	Real-time diagrammatic approach to transport through interacting quantum dots with normal and superconducting leads	Physical Review B	Vol. 77, no.13, 134513 (2008)
2008	N Camara, K Zekentes, V V Zelenin, P L Abramov, A V Kirillov, L P Romanov, N S Boltovets, V A Krivutsa, A Thuair, E Bano, E Tsoi and A A Lebedev	4H-SiC pn diodes grown by Sublimation Epitaxy in Vacuum (SEV) and their application as microwave diodes	Semicond. Sci. Technol.	Vol. 23, No 2, 025016/1-9 (February 2008)

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2008	S. Feruglio, F. Andrieu, O. Faynot, and G. Ghibaudo	In-depth Electrical Characterization of sub-45nm fully depleted strained SOI MOSFETs with TiN/HfO ₂ gate stack	Solid State Electronics	Vol. 52, no. 4, pp. 489-497 (Apr. 2008)
2008	F. Driussi, D. Esseni, L. Selmi, P.E. Hellstrom, G. Malm, J. Hallstedt, M. Ostling, T.J. Grasby, D.R. Leadley, X. Mescot	On the electron mobility enhancement in biaxially strained Si MOSFETs	Solid State Electronics	Vol. 52, no. 4, pp. 498-505 (2008)
2008	Q. Rafhay, R. Clerc, G. Ghibaudo, G. Pananakakis	Impact of source-to-drain tunnelling on the scalability of arbitrary oriented alternative channel material nMOSFETs	Solid State Electronics	Vol. 52, no.10, Pages 1474-1481 (October 2008)
2008	S. Danaie, M. Marin, G. Ghibaudo	The physical origins of mismatch in Si/SiGe : C heterojunction bipolar transistors for BiCMOS technologies	Solid State Electronics	Vol. 52, no.2, pp.323-337 (Feb. 2008)
2008	Q. Rafhay, R. Clerc, M. Ferrier, G. Pananakakis and G. Ghibaudo,	Impact of Channel Orientation on Ballistic Current of nDGFETs with Alternative Channel Materials	Solid State Electronics	Vol. 52, no.4, Pages 540-547 (April 2008)
2008	M. Braccioli, P. Palestri, M. Mouis, T. Poiroux, M. Vinet, G. Le Carval, C. Fiegna, E. Sangiorgi, S. Deleonibus	Monte-Carlo simulation of MOSFETs with band-offsets in the source and drain	Solid State Electronics	Vol. 52, no.4, pp. 506-13. Publisher: Elsevier Science Ltd., UK (April 2008)
2008	C. Dupré, T. Ernst, V. Maffini-Alvaro, V. Delaye, J.-M. Hartmann, S. Borel, C. Vizioz, O. Faynot, G. Ghibaudo and S. Deleonibus	3D nanowire gate-all-around transistors: Specific integration and electrical features	Solid State Electronics	Vol. 52, no.4, pp. 519-525 (Apr. 2008)
2008	V. Dobrovolsky, F. Sizov, S. Cristoloveanu, S. Pavljuk	Silicon on insulator avalanche-impact-ionization transistor with very low switching voltage from ON state to OFF state	Solid State Electronics	Vol. 52, no.7, 1047--1051 (2008)